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# FDP2D3N10C / FDPF2D3N10C

## N-Channel Shielded Gate PowerTrench® MOSFET

100 V, 222 A, 2.3 mΩ

### Features

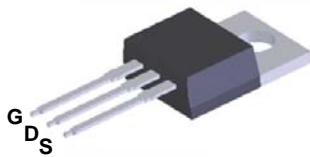
- Max  $r_{DS(on)}$  = 2.3 mΩ at  $V_{GS} = 10$  V,  $I_D = 100$  A
- Extremely Low Reverse Recovery Charge,  $Q_{rr}$
- 100% UIL Tested
- RoHS Compliant

### General Description

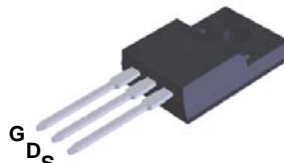
This N-Channel MV MOSFET is produced using ON Semiconductor's advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized to minimize on-state resistance and yet maintain superior switching performance with best in class soft body diode.

### Applications

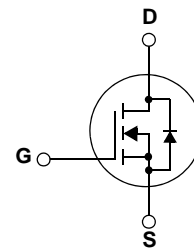
- Synchronous Rectification for ATX / Server / Telecom PSU
- Motor drives and Uninterruptible Power Supplies
- Micro Solar Inverter



TO-220



TO-220F



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Ratings		Units
		FDP2D3N10C	FDPF2D3N10C	
$V_{DS}$	Drain to Source Voltage	100	100	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	$\pm 20$	V
$I_D$	Drain Current -Continuous	$T_C = 25^\circ\text{C}$ (Note 3)	222*	A
	-Continuous	$T_C = 100^\circ\text{C}$ (Note 3)	157*	
	-Pulsed	(Note 1)	888	
$E_{AS}$	Single Pulse Avalanche Energy	(Note 2)	1176	mJ
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	214	W
	Power Dissipation	$T_A = 25^\circ\text{C}$	2.4	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +175		$^\circ\text{C}$

\* Drain current limited by maximum junction temperature. Package limitation current is 120A.

### Thermal Characteristics

Symbol	Parameter	FDP2D3N10C	FDPF2D3N10C	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.7	3.3	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	

### Package Marking and Ordering Information

Device Marking	Device	Package	Packing Method	Quantity
FDP2D3N10C	FDP2D3N10C	TO-220	Tube	50 units
FDPF2D3N10C	FDPF2D3N10C	TO-220F	Tube	50 units

**Electrical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}, V_{GS} = 0\text{ V}$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		70		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = 80\text{ V}, T_J = 150\text{ }^\circ\text{C}$			1 500	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 700\text{ }\mu\text{A}$	2.0	3.0	4.0	V
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 100\text{ A}$		2.1	2.3	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 100\text{ A}$		222		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		7980	11180	pF
$C_{oss}$	Output Capacitance			4490	6290	pF
$C_{rss}$	Reverse Transfer Capacitance			40	75	pF
$R_g$	Gate Resistance		0.1	0.8	1.8	$\Omega$

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{ V}, I_D = 100\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		42	67	ns
$t_r$	Rise Time			35	56	ns
$t_{d(off)}$	Turn-Off Delay Time			74	118	ns
$t_f$	Fall Time			32	57	ns
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V to } 10\text{ V}$ $V_{DD} = 50\text{ V},$ $I_D = 100\text{ A}$		108	152	nC
$Q_{gs}$	Gate to Source Gate Charge			36		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			22		nC
$Q_{oss}$	Output Charge	$V_{DD} = 50\text{ V}, V_{GS} = 0\text{ V}$		297		nC

**Drain-Source Diode Characteristic**

$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	222	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	888	A
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_{SD} = 100\text{ A}$		0.9	1.3	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, V_{DD} = 50\text{ V},$ $I_F = 100\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}$		107	172	ns
$Q_{rr}$	Reverse Recovery Charge			191	306	nC
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, V_{DD} = 50\text{ V},$ $I_F = 100\text{ A}, di_F/dt = 300\text{ A}/\mu\text{s}$		97	155	ns
$Q_{rr}$	Reverse Recovery Charge			492	788	nC

Notes:

1. Pulsed  $I_D$  please refer to Figure.11 and Figure.12 "Forward Bias Safe Operating Area" for more details.
2.  $E_{AS}$  of 1176 mJ is based on starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 3\text{ mH}$ ,  $I_{AS} = 28\text{ A}$ ,  $V_{DD} = 90\text{ V}$ ,  $V_{GS} = 10\text{ V}$ . 100% test at  $L = 0.1\text{ mH}$ ,  $I_{AS} = 89\text{ A}$ .
3. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.

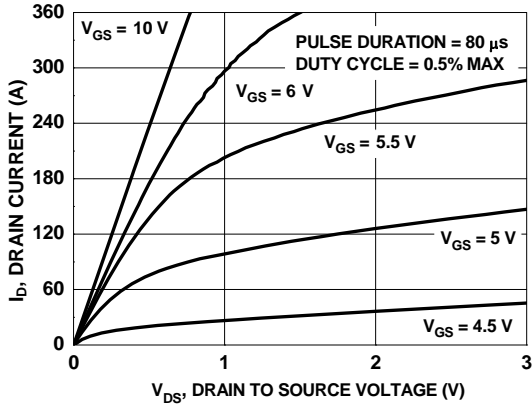


Figure 1. On-Region Characteristics

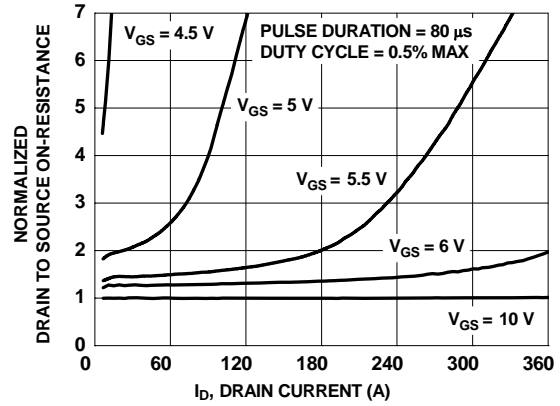


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

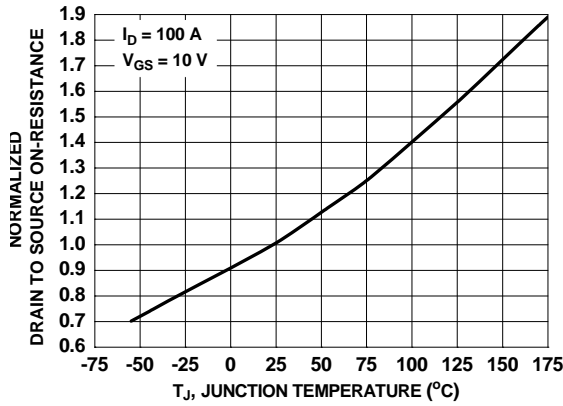


Figure 3. Normalized On-Resistance vs. Junction Temperature

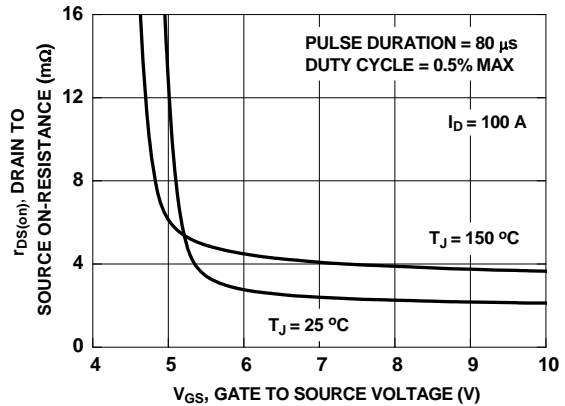


Figure 4. On-Resistance vs. Gate to Source Voltage

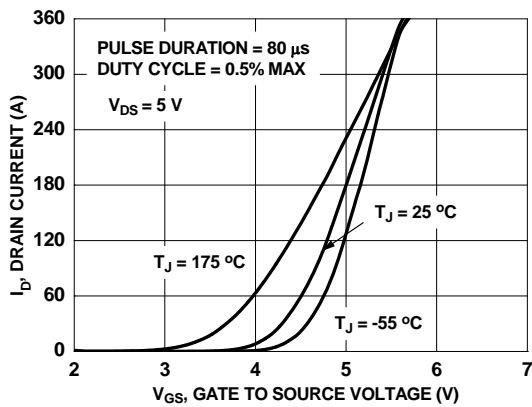


Figure 5. Transfer Characteristics

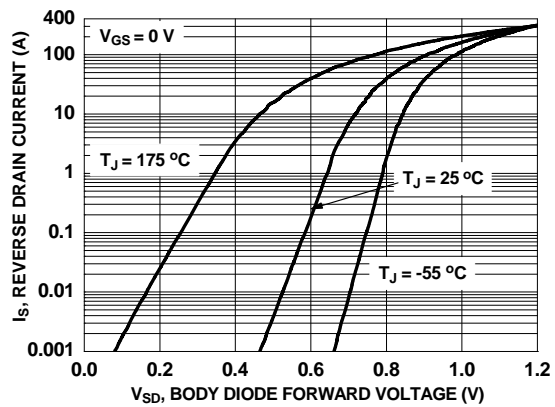
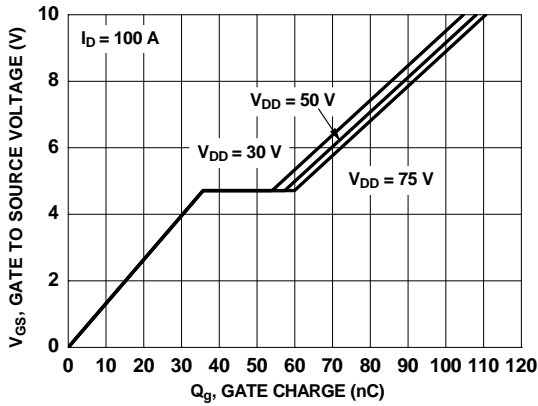
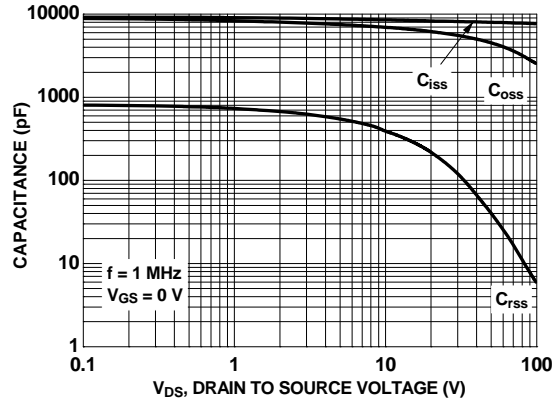


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

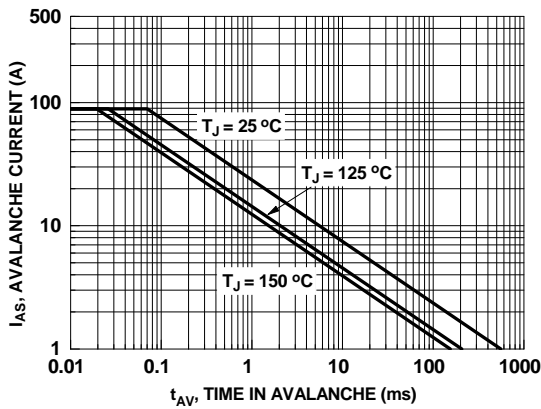
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.



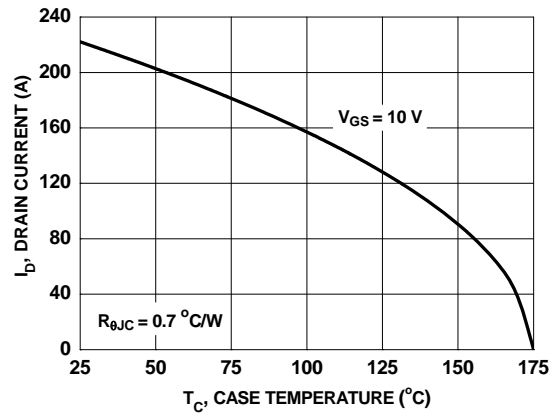
**Figure 7. Gate Charge Characteristics**



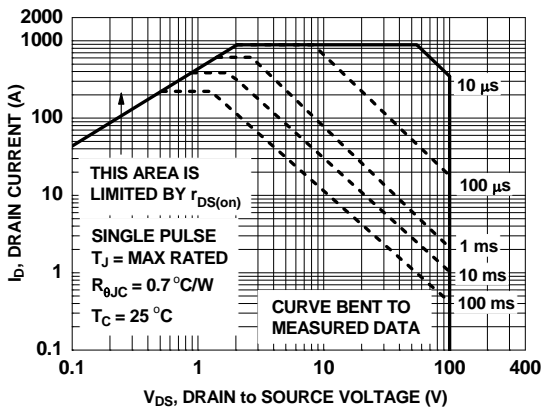
**Figure 8. Capacitance vs. Drain to Source Voltage**



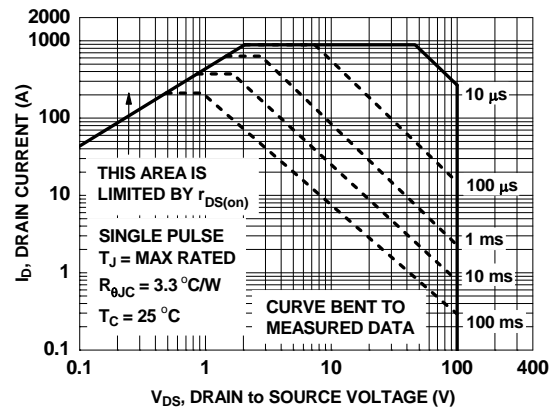
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**

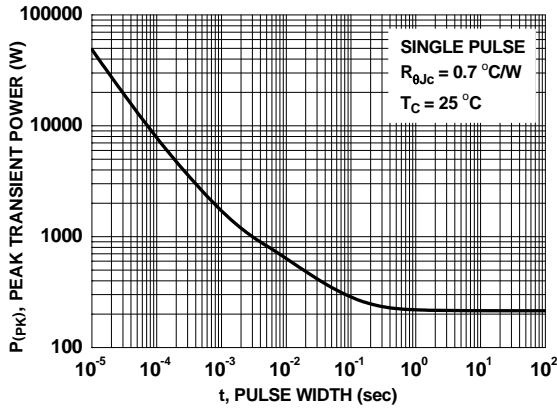


**Figure 11. Forward Bias Safe Operating Area for FDP2D3N10C**

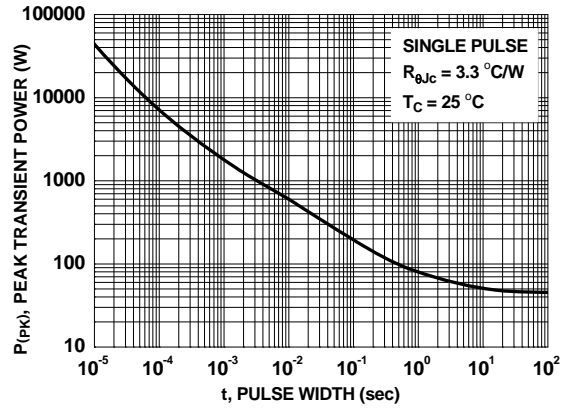


**Figure 12. Forward Bias Safe Operating Area for FDPF2D3N10C**

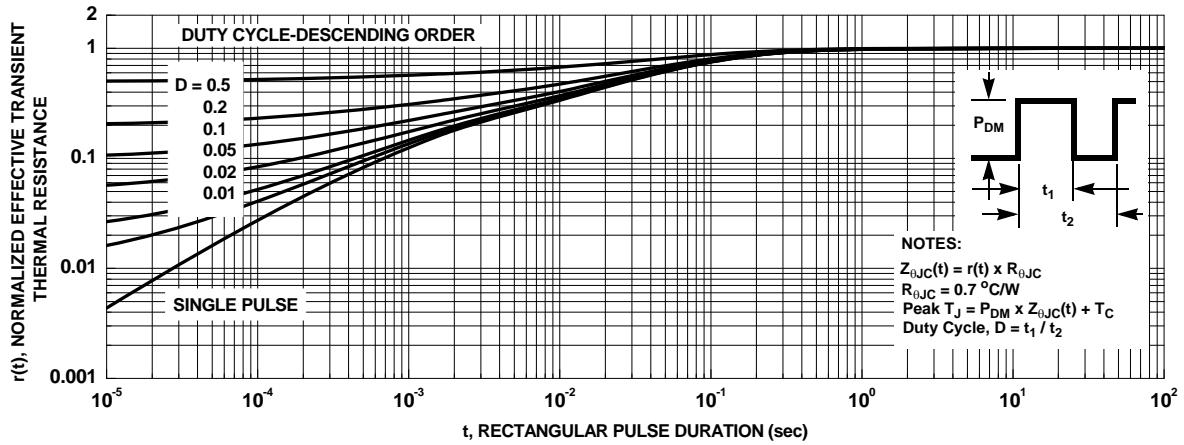
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.



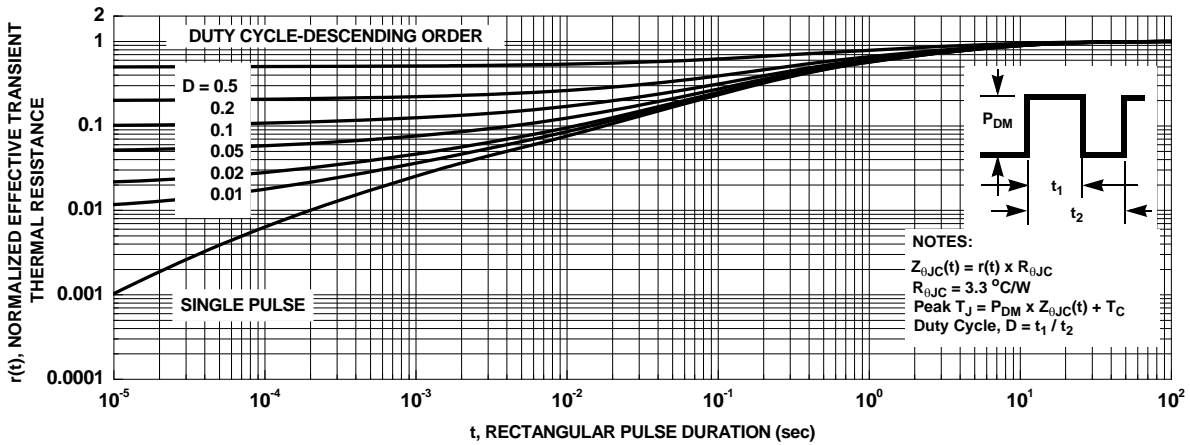
**Figure 13. Single Pulse Maximum Power Dissipation for FDP2D3N10C**



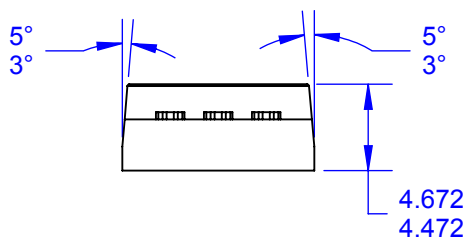
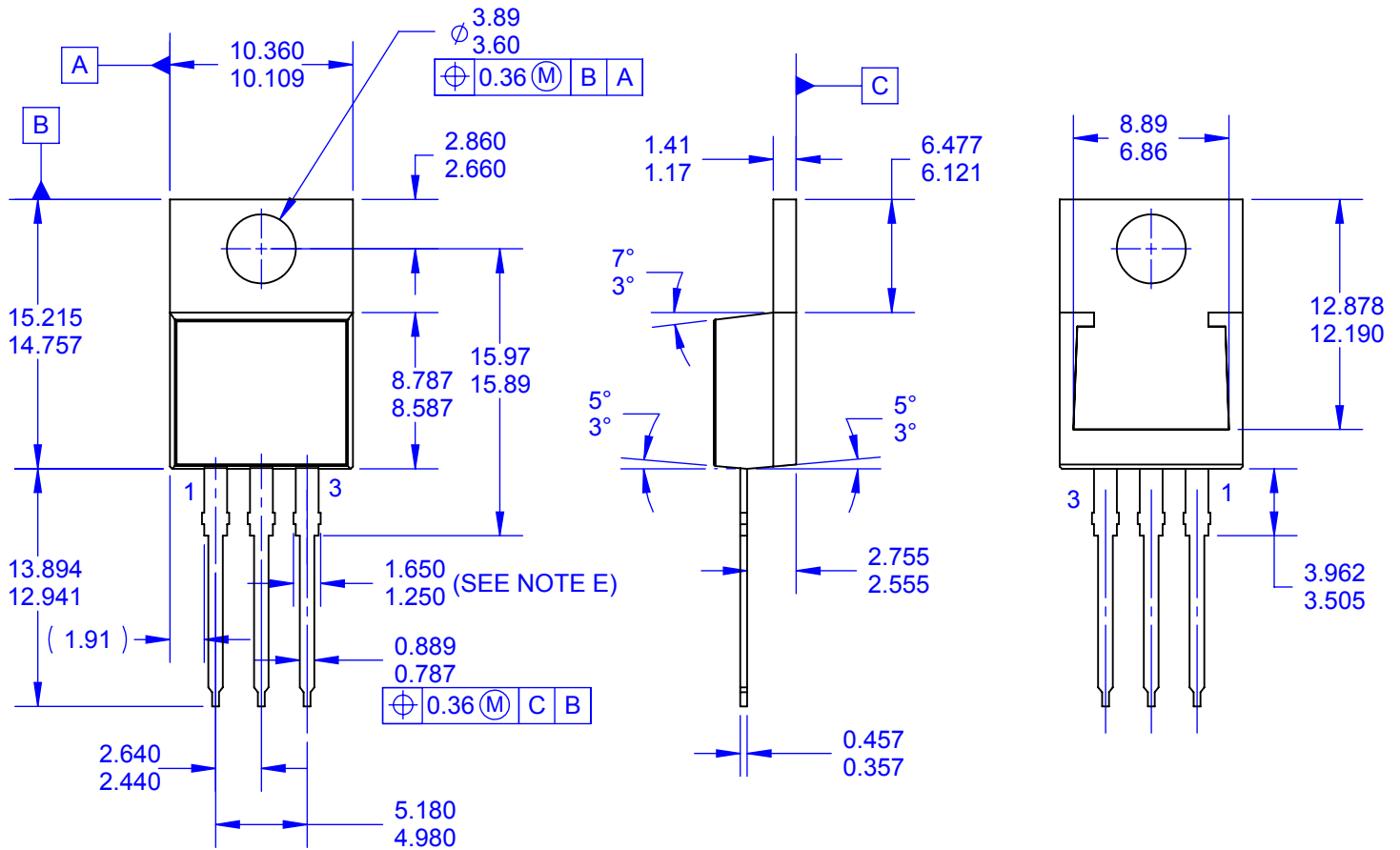
**Figure 14. Single Pulse Maximum Power Dissipation for FDPF2D3N10C**



**Figure 15. Junction-to-Case Transient Thermal Response Curve for FDP2D3N10C**

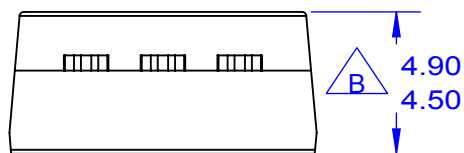
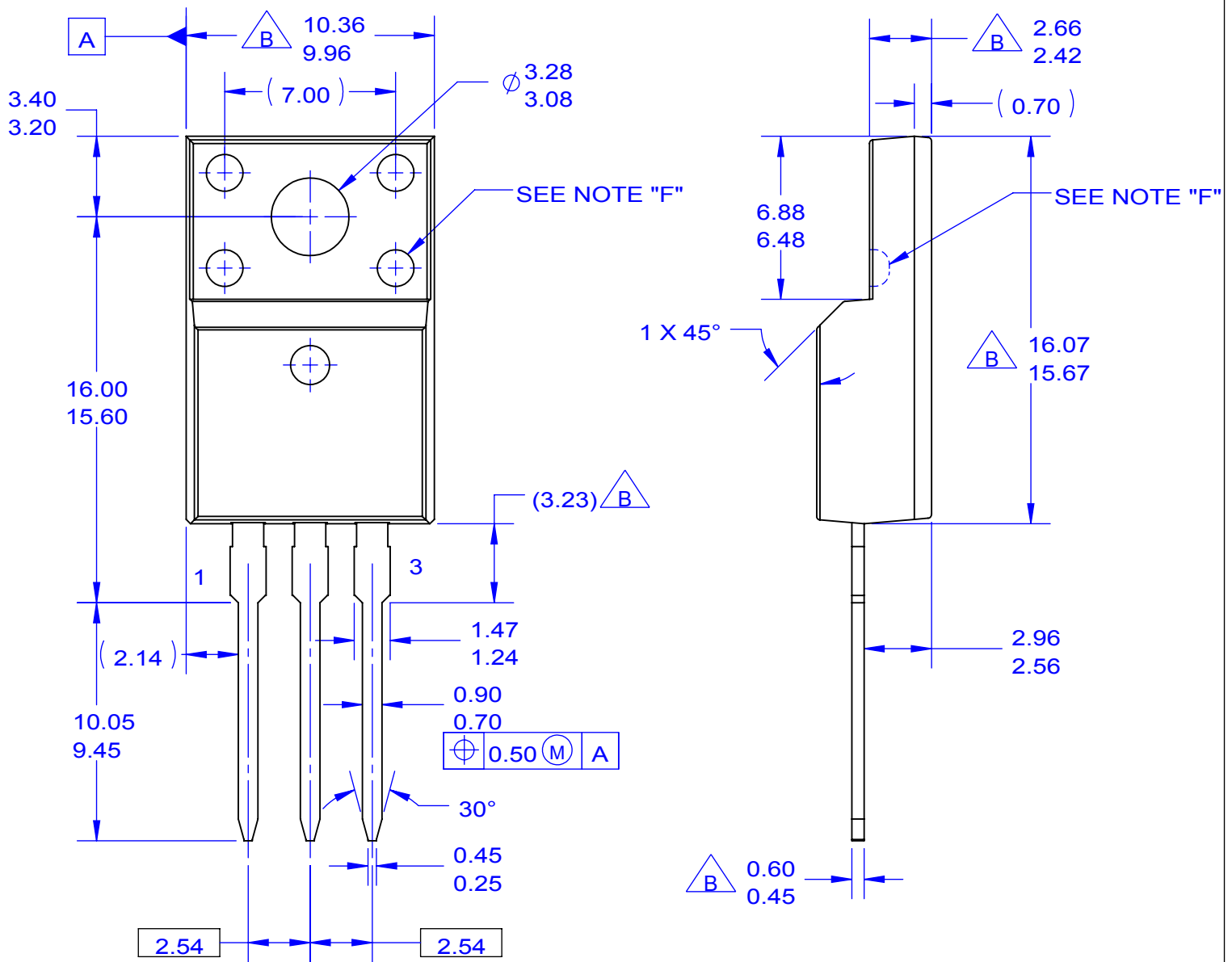


**Figure 16. Junction-to-Case Transient Thermal Response Curve for FDPF2D3N10C**



**NOTES:**

- A. PACKAGE REFERENCE: JEDEC TO220 VARIATION AB
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. MAX WIDTH FOR F102 DEVICE = 1.35mm.
- F. DRAWING FILE NAME: TO220T03REV4.
- G. FAIRCHILD SEMICONDUCTOR.



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NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.  
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV5



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